

Silicon Switching Diode

**1N4153,
1N4153-1**

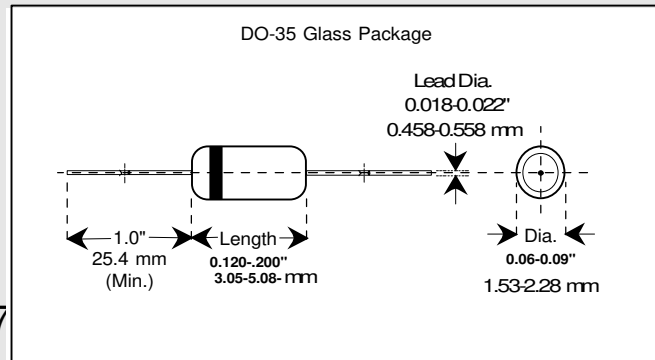
DO-35 Glass Package

Applications

Used in general purpose applications, where a low current controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Full approval to Mil-S-19500/337
- Available up to JANTXV-1 levels
- "S" level screening available to SCDs



Maximum Ratings		Symbol	Value	Unit	
Peak Inverse Voltage		PIV	75 (Min.)	Volts	
Average Rectified Current		I _{Avg}	150	mAmps	
Continuous Forward Current		I _{Fdc}	300	mAmps	
Peak Surge Current (t _{peak} = 1 Sec.)		I _{peak}	0.25	Amp	
BKC Power Dissipation T _L = 50 °C, L = 3/8" from body		P _{tot}	500	mWatts	
Operating and Storage Temperature Range		T _{Op & St}	-65 to +200	°C	
Electrical Characteristics @ 25 °C*		Symbol	Minimum	Maximum	Unit
Forward Voltage @ I _F = 100 μA	V _F	V _f	0.49	0.55	Volts
Forward Voltage @ I _F = 250 μA	V _F	V _f	0.53	0.59	Volts
Forward Voltage @ I _F = 1.0 mA	V _F	V _f	0.59	0.67	Volts
Forward Voltage @ I _F = 2.0 mA	V _F	V _f	0.62	0.70	Volts
Forward Voltage @ I _F = 10 mA	V _F	V _F	0.70	0.81	Volts
Forward Voltage @ I _F = 20 mA	V _F	V _F	0.74	0.88	Volts
Reverse Leakage Current @ V _R = 50 V	I _R			0.05(50 @ 150 °C)	μA
Breakdown Voltage @ I _R = 5.0 μA	PIV		75		Volts
Capacitance @ V _R = 0 V, f = 1mHz	C _T			2.0	pF
Reverse Recovery Time (note 1)	t _{rr}			4.0	nSecs
Reverse Recovery Time (note 2)	t _{rr}			2.0	nSec

Note 1: Per Method 4031-A with $I_F = I_R = 10 \text{ mA}$, $R_L = 100 \text{ Ohms}$, $C = 3 \text{ Pf}$. *Unless Otherwise Specified

Note2: Per Method 4031-A with $I_F = I_R = 10 \text{ mA}$, $R_r = 6 \text{ Volts}$, $R_l = 100 \text{ ohms}$.



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